





APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/425,694	10/22/1999	ROLAND BRUNNER	BRUNNER-ET-A	9906
75	90 04/10/2002			
COLLARD & ROE PC			EXAMINER	
1077 NORTHE ROSLYN, NY	RN BLVD		BROWN, CHARLOTTE A	
			ART UNIT	PAPER NUMBER
			1765	24
			DATE MAILED: 04/10/2002	~~

Please find below and/or attached an Office communication concerning this application or proceeding.

Application No. 09/425,694

Applicant(s)

Brunner et al.

## Office Action Summary

Examiner

Charlotte A. Brown

Art Unit **1765** 

	The MAILING DATE of this communication appears on	the cover sheet with the correspondence address	
THE N - Exten aft - If the be - If NO co - Failur	ORTENED STATUTORY PERIOD FOR REPLY IS SET IN INCIDENT ALLING DATE OF THIS COMMUNICATION.  IS Signs of time may be available under the provisions of 37 CFR or SIX (6) MONTHS from the mailing date of this communicat period for reply specified above is less than thirty (30) days, a considered timely.  Period for reply is specified above, the maximum statutory per mmunication.	1.136 (a). In no event, however, may a reply be timely filed	
Status 1) 💢	Responsive to communication(s) filed on <u>Feb 15, 20</u>	02	
2a) 🗌	This action is <b>FINAL</b> . 2b) 💢 This action		
3)	and the second time for allowance except for formal matters, prosecution as to the merits is		
Disposi	tion of Claims	is lorg pending in the application.	
4) 💢	Claim(s) <u>1-11</u>	is/are pending in the application.	
•	4a) Of the above, claim(s)	is/are withdrawn from consideration.	
5) 🗆	Claim(s)	is/are allowed.	
6) X	Claim(s) 1-11	is/are rejected.	
7) 🗆	Claim(s)	is/are objected to.	
8) 🗆	Claims	are subject to restriction and/or election requirement.	
Applic 9) ☐ 10) ☐ 11) ☐ 12) ☐	The drawing(s) filed on is/are The proposed drawing correction filed on	is: a) $\square$ approved b) $\sqcup$ disapproved.	
13)⊠ a)	see the attached detailed Office action for a list of the	ve been received.  ve been received in Application No  locuments have been received in this National Stage sau (PCT Rule 17.2(a)).  ne certified copies not received.	
Attack	nment(s)		
Į.	Notice of References Cited (PTO-892)	18) Interview Summary (PTO-413) Paper No(s).	
	Notice of Draftsperson's Patent Drawing Review (PTO-948)	19) Notice of Informal Patent Application (PTO-152)	
	Information Disclosure Statement(s) (PTO-1449) Paper No(s).	20) Other:	

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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Pirooz (EP 0731498 A2) in view of Verhaverbeke et al. (US 6,132,522).

From line 32 of column 2 to the end of column 3 , Pirooz discloses a method for treating a silicon wafer which includes the step of contacting the surface of the silicon wafer with an aqueous solution containing hydrofluoric acid to remove the metals from the wafer surface. The removal is carried out by contacting the silicon wafers with an aqueous solution containing about 1:1 to 1:10,000 parts by volume HF: $H_2O$ . To enhance the metals removal, the solution may additionally contain HCl,  $H_2O_2$  OR  $O_3$  (Column 2, lines 49-54). This reads on the applicant's limitation of firstly treating the semiconductor wafers in a bath with an aqueous HF solution and optionally containing HCl and optionally a surfactant. Next, the wafers are contacted with high

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purity ozonated water containing ozone (Column 3, lines 14-15). This reads on the applicant's limitation of treating the wafers in a bath with an aqueous O<sub>3</sub> solution only containing O<sub>3</sub>. The aqueous ozone solution may additionally contain hydrochloric acid (HCl) or nitric acid. (Column 3, lines 32-34). After the metals removal, the silicon wafers are rinsed in deionized water (Column 3, lines 8-10). The final step of the cleaning process is drying the oxidized wafers. The wafers may be dried using any method which does not recontaminate the wafers with metals or other contaminants. Such methods include conventional spin drying and isopropyl alcohol vapor drying techniques which are well known in the field.

Unlike the claimed invention, Pirooz does not disclose a method for forming the treatment sequence  $B_2$  by treating the semiconductor wafer with an aqueous  $O_3$  solution and then treating the semiconductor wafers in a bath with an aqueous HCl solution only containing HCl. Since Pirooz first treats the semiconductor wafer with an ozone in water and then optionally adds hydrochloric acid, it is the Examiner's position that a person having ordinary skill in the art would have found it obvious to modify Pirooz's procedure by treating the semiconductor wafers with  $O_3$ , and then treating the wafers with a liquid containing HCl in a separate bath in order to produce a more efficient procedure for removing the metals from the surface of the semiconductor wafers thereby enhancing the metals removal.

Unlike the claimed invention, Pirooz does not form a treatment sequence which forms a treatment sequence which avoids rinsing with water or another treatment liquid.

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Verhaverbeke discloses wet processing methods for the manufacture of semiconductor wafers. The wet processing methods are applicable to any wet processing equipment including wet benches, baths, or spray cleaning systems. The wafers are exposed to reactive chemical process fluids by being sequentially immersed in reactive chemical process fluids (Column 5, lines 39-45). Traditionally, a DI water rinse is performed between each chemical treatment step (Column 10, lines 19-21). The present invention departs from this principle by not performing a DI water rinse between each chemical treatment step. This obtains good process performance and leads to overall cost efficiency (Column 10, lines 30-35).

It is the Examiner's position that a person having ordinary skill in the art would have found it obvious to modify Pirooz by avoiding rinsing with water or another treatment liquid as taught by Verhaverbeke. The method of eliminating the water rinse would have been anticipated in order to obtain good process performance (Column 10, lines 30-35). Therefore, the step of rinsing with water between process steps is an optional step that would not need to be performed.

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. (EP 0731498A2)

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4. Any inquiry concerning this communication from the Examiner should be directed to Charlotte A. Brown whose telephone number is 703-305-0727. The Examiner can normally be reached during the hours of 9:00AM to 6:30PM.

The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9310 for regular communications and 703-872-9311 for After final communications.

CAB

April 8, 2002

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